53. (New) A method of processing a wafer comprising:

receiving a wafer within a workpiece processing apparatus;

supporting the wafer using a workpiece holder of the workpiece processing apparatus;

coupling circuitry of the wafer with circuitry of the workpiece holder;

processing the wafer within the workpiece processing apparatus to form at least one semiconductor device; and

communicating signals intermediate the circuitry of the wafer and the circuitry of the workpiece holder.

54. (New) The method in accordance with claim 53 wherein the coupling comprises coupling the circuitry of the wafer and the circuitry of the workpiece holder at an interface of a surface of the wafer and a surface of the workpiece holder.

55. (New) The method in accordance with claim 53 wherein the receiving comprises receiving a semiconductive wafer.

56. (New) The method in accordance with claim 53 further comprising altering the processing responsive to the communicating.

A2 cont.

57. (New) The method in accordance with claim 53 wherein the communicating comprises communicating during the processing.

58. (New) The method in accordance with claim 53 further comprising communicating the signals using an intermediate member of the workpiece processing apparatus.

59. (New) The method in accordance with claim 53 wherein the coupling comprises contacting the circuitry of the wafer and the circuitry of the workpiece holder.

60. (New) A method of processing a workpiece comprising:

receiving a workpiece within a workpiece processing apparatus configured to form a semiconductor device using the workpiece;

processing the workpiece within the workpiece processing apparatus to form the semiconductor device; and

communicating signals intermediate the workpiece and the workpiece processing apparatus.

61. (New) The method in accordance with claim 60 further comprising electrically coupling the workpiece and the workpiece processing apparatus.

A

A2 cont.

62. (New) The method in accordance with claim 61 wherein the coupling comprises contacting circuitry of the workpiece and circuitry of the apparatus.

63. (New) The method in accordance with claim 60 further comprising:

supporting a workpiece using a workpiece holder of the workpiece processing apparatus; and

coupling circuitry of the workpiece and circuitry of the workpiece holder at an interface of a surface of the workpiece and a surface of the workpiece holder.

64. (New) The method in accordance with claim 60 wherein the receiving comprises receiving the workpiece comprising a semiconductive wafer.

65. (New) The method in accordance with claim 60 further comprising altering the processing responsive to the communicating.

66. (New) The method in accordance with claim 60 wherein the communicating comprises communicating during the processing.

A

A2 cont.

67. (New) The method in accordance with claim 60 further comprising communicating the signals using an intermediate member of the workpiece processing apparatus.

68. (New) A method of communicating signals with respect to a wafer comprising:

providing a workpiece holder;

supporting a wafer using the workpiece holder;

coupling circuitry of the wafer with circuitry of the workpiece holder; and

communicating signals intermediate the circuitry of the wafer and the circuitry of the workpiece holder.

69. (New) The method in accordance with claim 68 wherein the providing the wafer comprises providing a semiconductive wafer.

70. (New) The method in accordance with claim 68 wherein the coupling comprises coupling the circuitry of the wafer and the circuitry of the workpiece holder at an interface of a surface of the wafer and a surface of the workpiece holder.

A

A2 cont.

71. (New) The method in accordance with claim 68 wherein the coupling comprises contacting the circuitry of the wafer and the circuitry of the workpiece holder.

72. (New) The method in accordance with claim 68 wherein the communicating comprises communicating using an intermediate member.

73. (New) A method of communicating signals within a workpiece processing apparatus comprising:

providing a workpiece processing apparatus adapted to process a workpiece to form a semiconductor device;

providing a workpiece within the workpiece processing apparatus;

communicating signals using the workpiece; and

receiving the signals within the workpiece processing apparatus from the workpiece.

74. (New) The method in accordance with claim 73 further comprising coupling circuitry of the workpiece with circuitry of the workpiece processing apparatus.

A3 cont.

75. (New) The method in accordance with claim 74 wherein the coupling comprises contacting the circuitry of the workpiece with the circuitry of the workpiece processing apparatus.

76. (New) The method in accordance with claim 74 further comprising breaking the coupling of the circuitry of the workpiece and the circuitry of the workpiece processing apparatus.

77. (New) The method in accordance with claim 73 further comprising supporting the workpiece within the workpiece processing apparatus using a workpiece holder, and wherein the receiving comprises receiving using the workpiece holder.

78. (New) The method in accordance with claim 77 further comprising coupling circuitry of the workpiece and circuitry of the workpiece holder at an interface of a surface of the workpiece and a surface of the workpiece holder.

79. (New) The method in accordance with claim 73 further comprising supporting the workpiece within the workpiece processing apparatus using a workpiece holder and an intermediate member, and wherein the receiving comprises receiving using the workpiece holder and the intermediate member.

Aa
Conc.

80. (New) The method in accordance with claim 73 ~~wherein~~ the providing the workpiece ~~comprises~~ providing a semiconductive wafer.

B

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